DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)\ max}$	I_D T_A = +25°C
20V	0.9Ω @ V_{GS} = 4.5V	-430mA

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Load Switch

Features

- Dual P-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage $V_{GS(TH)}$ <1V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at https://www.diodes.com/products/automotive/automotive-products/.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. https://www.diodes.com/quality/product-definitions/**

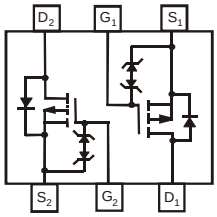
Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish - Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.006 grams (Approximate)

ESD PROTECTED

SOT363

Top View



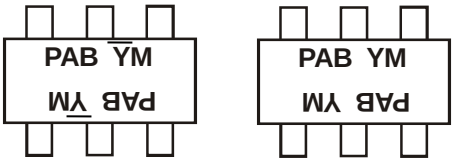
Top View
Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2004DWK-7	SOT363	3000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



PAB = Product Type Marking Code
$\overline{Y}$M or YM = Date Code Marking
Y or $\overline{Y}$ = Year (ex: H = 2020)
M = Month (ex: 9 = September)

Date Code Key

Year	2007	~	2020	2021	2022	2023	2024	2025	2026	2027
Code	U	~	H	I	J	K	L	M	N	O

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	-20	V
Gate-Source Voltage		V_{GSS}	±8	V
Drain Current (Note 5) VGS = -4.5V	T_A = +25°C T_A = +85°C	I_D	-430 -310	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_D	250	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	500	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1.0	µA	V_{DS} = -20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±1.0	µA	V_{GS} = ±4.5V, V_{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.5	—	-1.0	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	0.7 1.1 1.7	0.9 1.4 2.0	Ω	V_{GS} = -4.5V, I_D = -430mA V_{GS} = -2.5V, I_D = -300mA V_{GS} = -1.8V, I_D = -150mA
Forward Transfer Admittance	$\|Y_{fs}\|$	200	—	—	ms	V_{DS} = 10V, I_D = 0.2A
Diode Forward Voltage (Note 5)	V_{SD}	-0.5	—	-1.2	V	V_{GS} = 0V, I_S = 115mA
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	—	175	pF	V_{DS} = -16V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	—	30	pF	
Reverse Transfer Capacitance	C_{rss}	—	—	20	pF	

Notes: 5. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.
6. Short duration pulse test used to minimize self-heating effect.

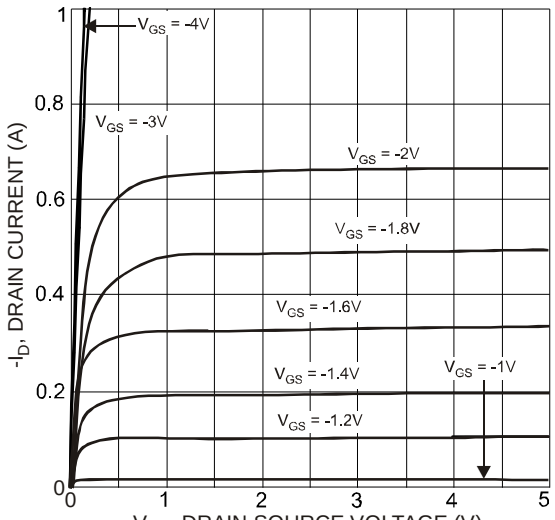


Fig. 1 Typical Output Characteristics

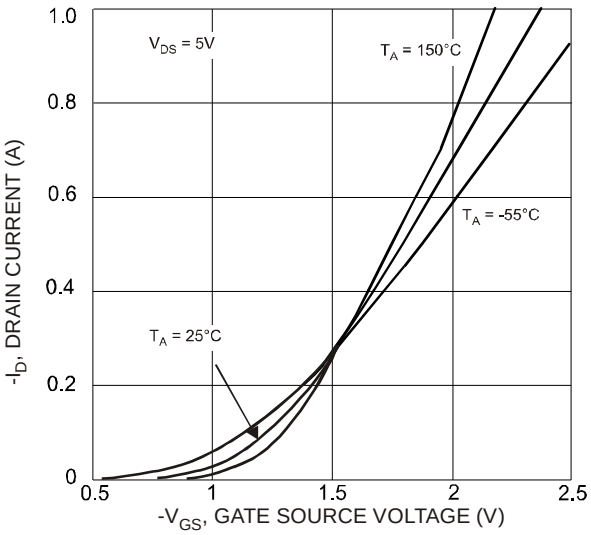


Fig. 2 Typical Transfer Characteristics

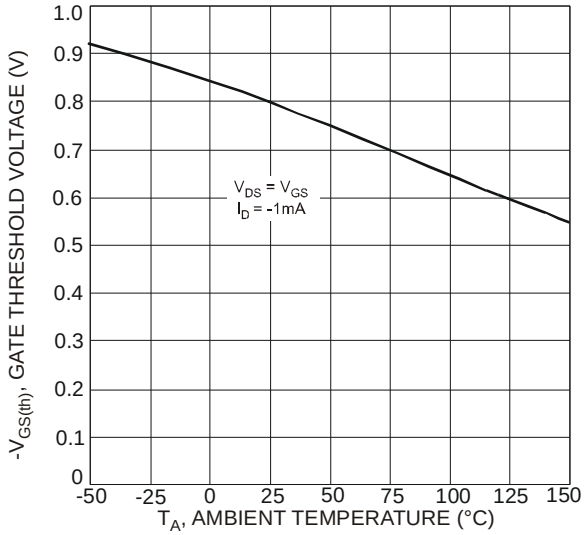


Fig. 3 Gate Threshold Voltage vs. Ambient Temperature

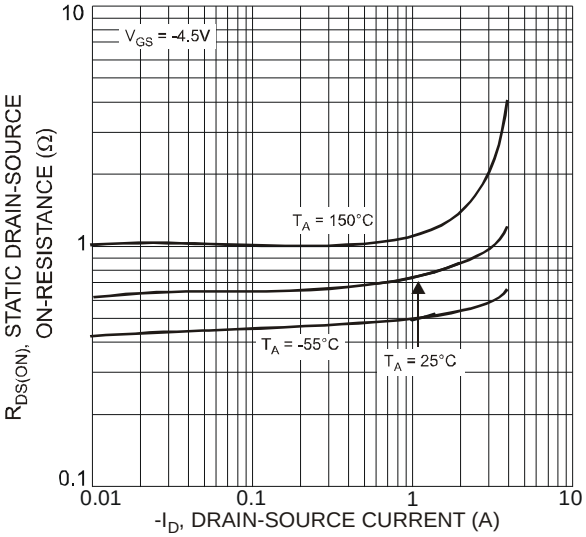


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

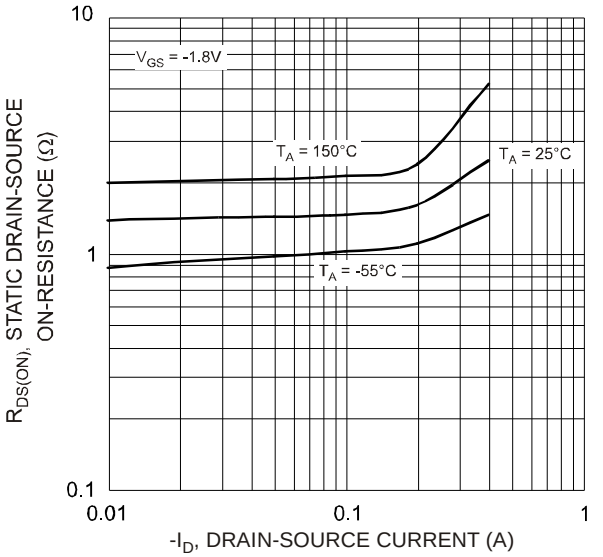


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

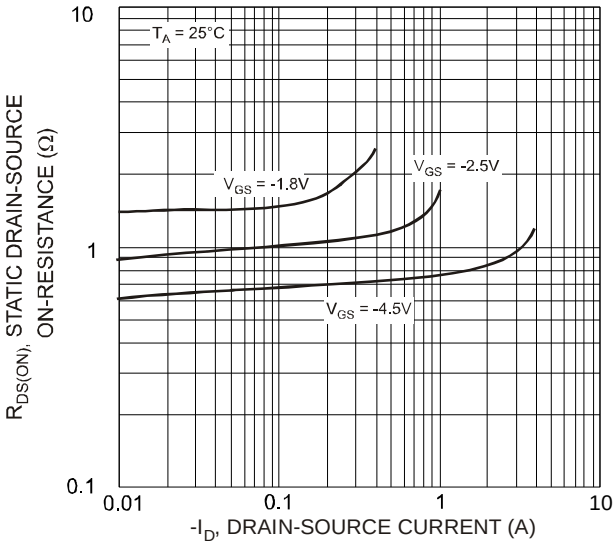


Fig. 6 Static Drain-Source On-Resistance vs. Drain-Source Current vs. Gate Source Voltage

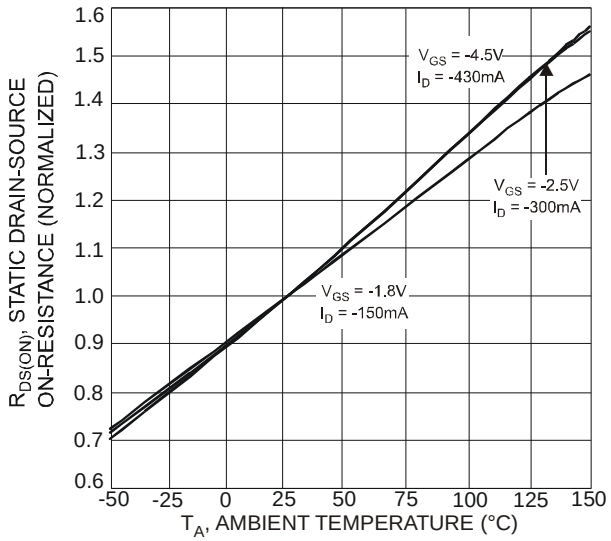


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

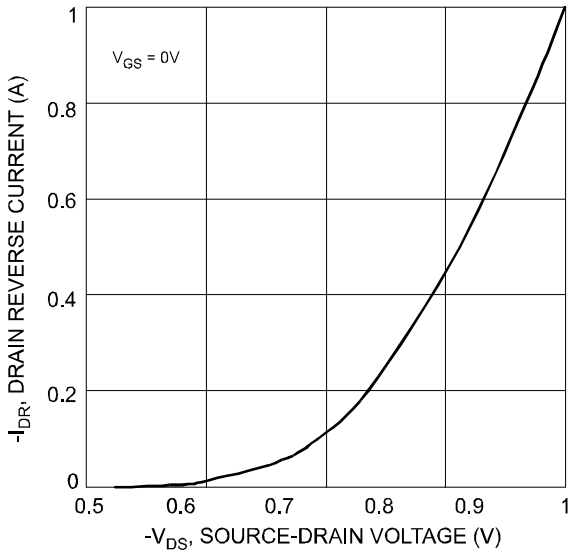


Fig. 8 Drain Reverse Current vs. Source-Drain Voltage

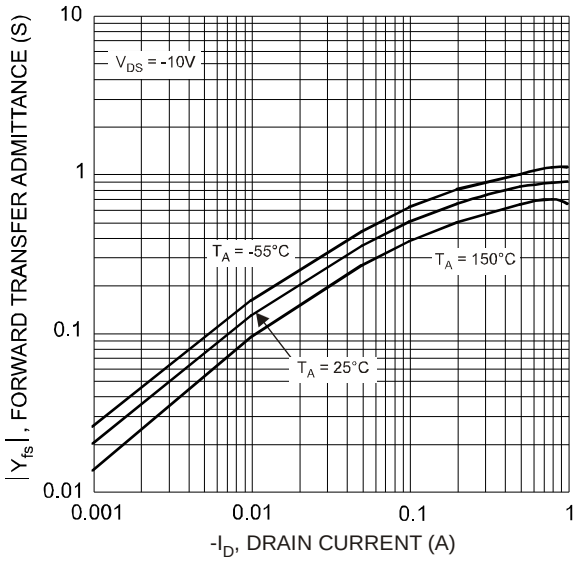


Fig. 9 Forward Transfer Admittance vs. Drain Current

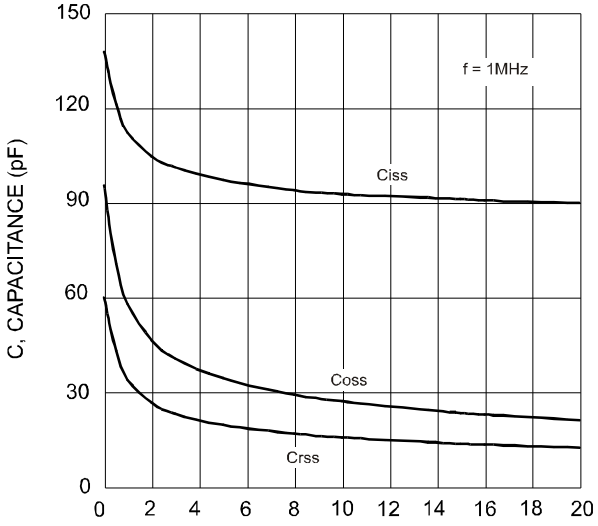
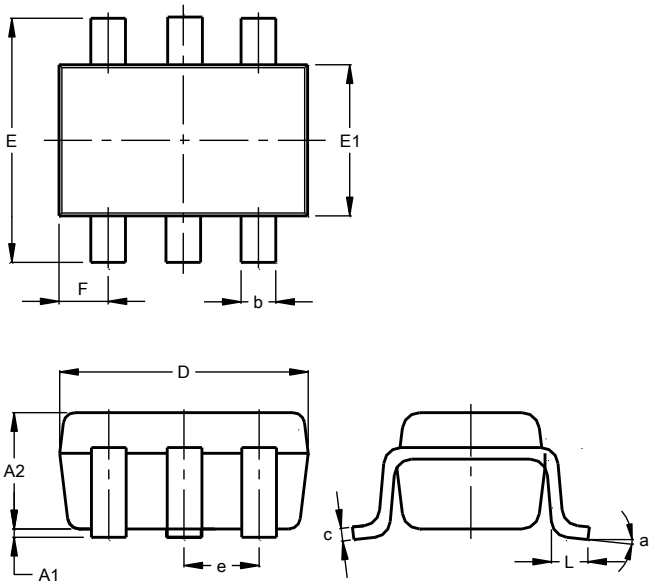


Fig. 10 Typical Capacitance

Package Outline Dimensions

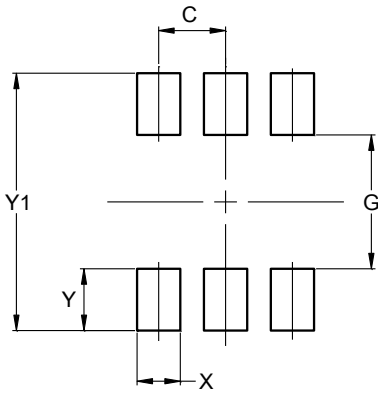
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT363			
Dim	**Min**	**Max**	**Typ**
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

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